

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. It is suitable for automotive application.

• Features

- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

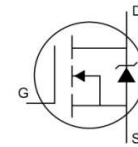
- BLDC Motor driver
- DC-DC
- Battery protection

• Ordering Information:

Part NO.	ZMS055N04HD
Marking	ZMS055N04H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

• Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

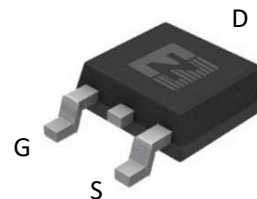
Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		40	V
Gate-Source Voltage	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	66	A
	I_D	$T_C=75^\circ\text{C}$	53	A
	I_D	$T_C=100^\circ\text{C}$	46	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$;	264	A
Total Power Dissipation	P_D	$T_C=25^\circ\text{C}$	65	W
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	2.4	W
Operating Junction Temperature	T_J		-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to +175	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	$L=0.1\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	40	mJ
		$L=0.5\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	76	mJ
ESD Level (HBM)	CLASS 1C			



$$V_{DS} = 40\text{V}$$

$$R_{DS(ON)} = 5.5\text{m}\Omega$$

$$I_D = 66\text{A}$$



TO-252



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	2.3	°C/W
Thermal resistance, junction-ambient	$R_{thJA\odot}$		-	62	°C/W
Soldering temperature (total time<10s)	Tsold		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0	2.7	4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=40V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=14A$		5.5	7.1	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_{SD}=4A$		7		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=14A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V$	-	908	-	pF
Output capacitance	C_{oss}		-	244	-	
Reverse transfer capacitance	C_{rss}		-	10	-	
Gate Resistance	R_g	$f=1MHz$	-	1.2		Ω
Total gate charge	Q_g	$V_{DD}=15V, I_D=20A, V_{GS}=10V$	-	14	-	nC
Gate - Source charge	Q_{gs}		-	3.2	-	
Gate - Drain charge	Q_{gd}		-	3.5	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=20A$	-	5	-	ns
Turn-ON Rise time	t_r		-	10	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	8	-	ns
Turn-Off Fall time	t_f		-	3	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD}=20V, dI_S/dt=100A/\mu s, I_S=50A$	-	30	-	ns
Reverse Recovery Charge	Q_{RR}		-	21	-	nC

Fig.1 Gate-Charge Characteristics

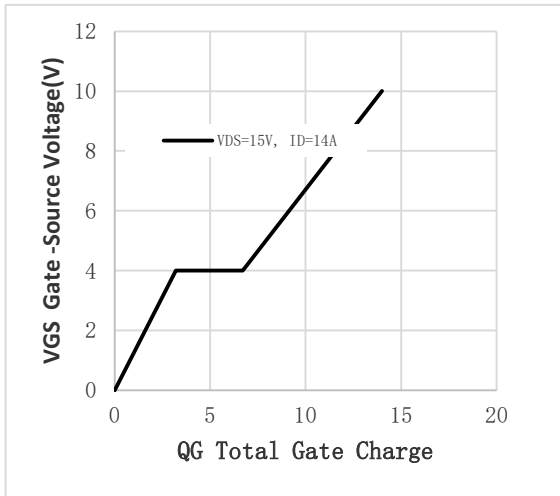


Fig.2 Capacitance Characteristics

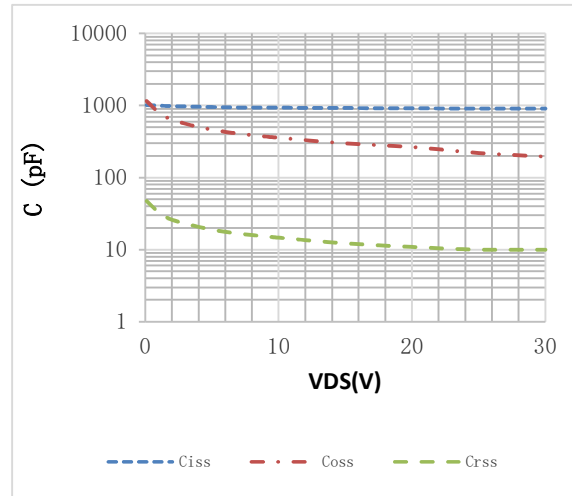


Fig.3 Power Dissipation

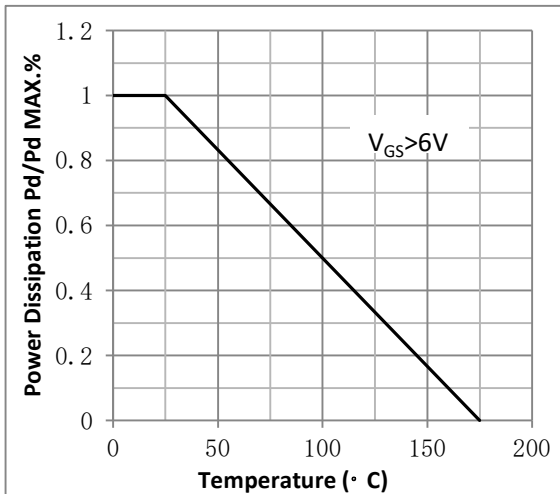


Fig.4 Typical output Characteristics

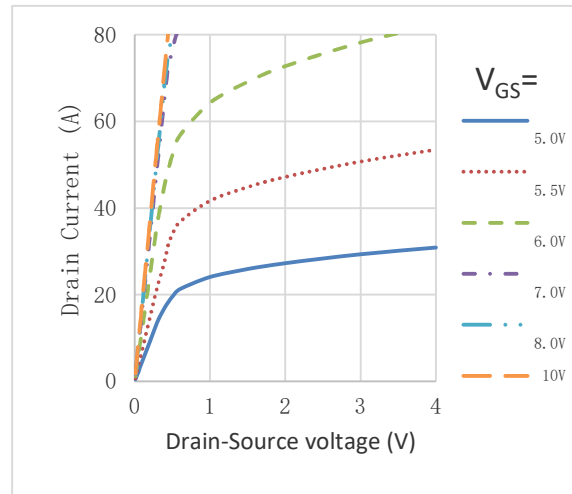


Fig.5 Threshold Voltage V.S Junction Temperature

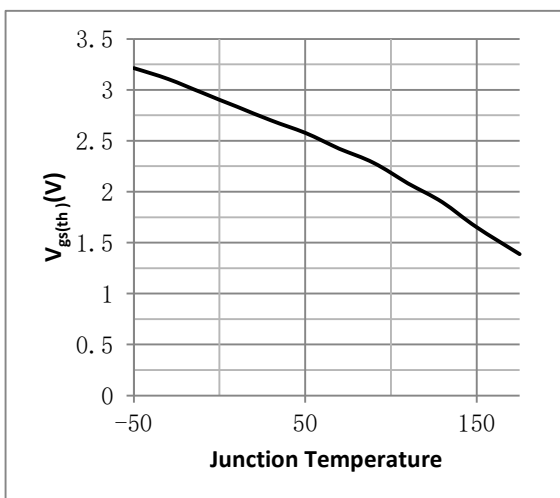


Fig.6 Resistance V.S Drain Current

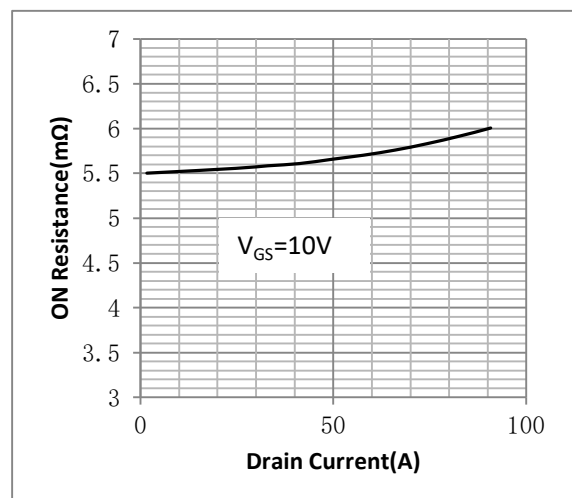


Fig.7 On-Resistance VS Gate Source Voltage

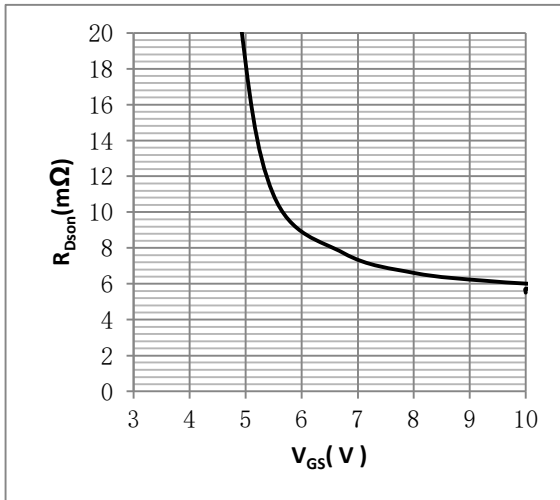


Fig.8 On-Resistance V.S Junction Temperature

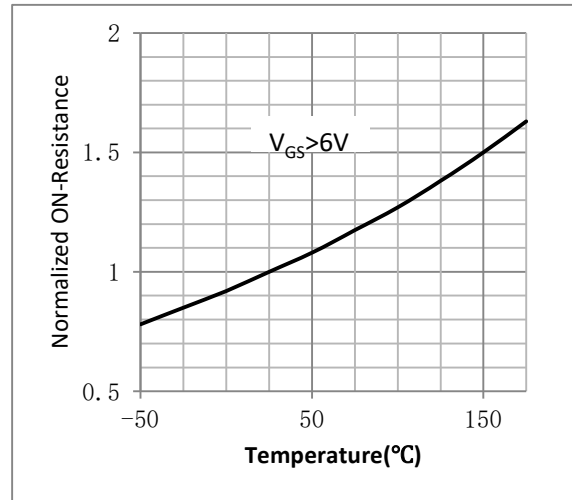


Figure 9. Diode Forward Voltage vs. Current

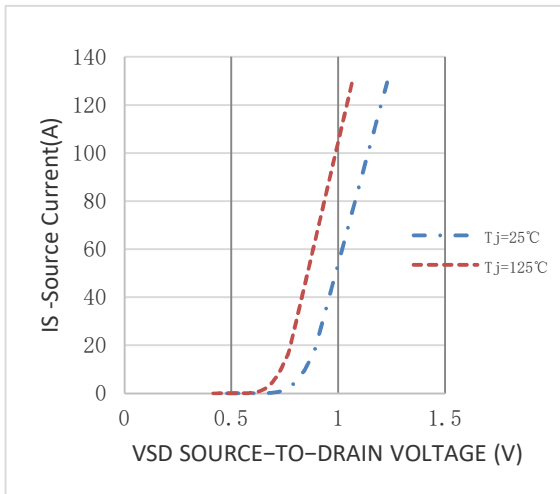


Figure 10. Transfer Characteristics

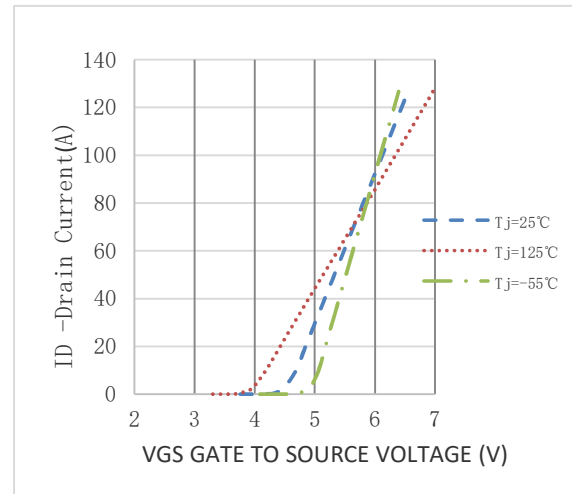


Fig.11 Safe Operating Area

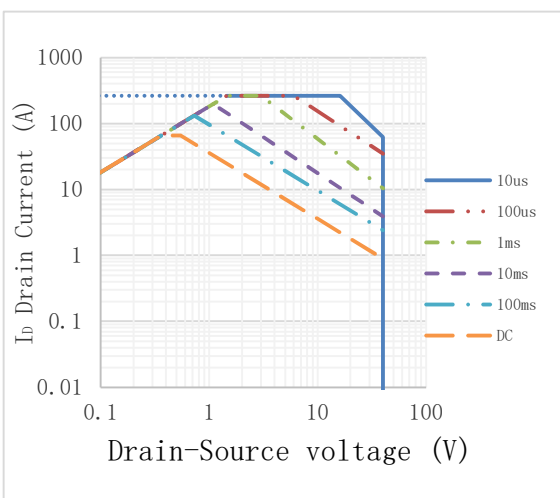
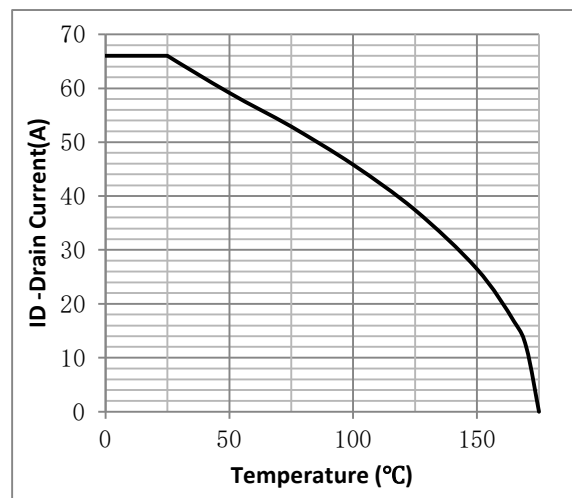
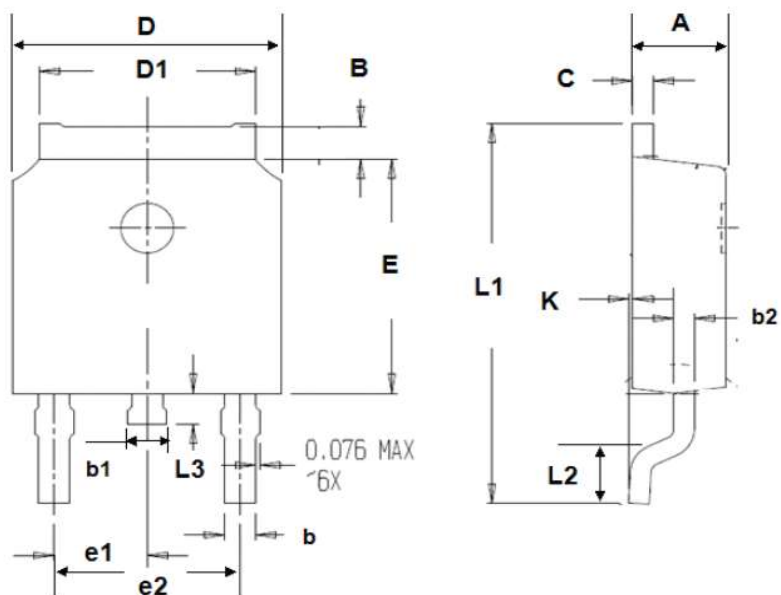


Fig.12 ID vs. Junction Temperature[®]



•TO-252 Package Outline

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.90	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.24	2.35
L1	9.20	10.60	e2	4.43	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			



Note:

① Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

② Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2022.1.6	
B	2022.9.26	1.Add Dynamic characteristic t_f , t_r etc.
C	2023.12.19	Correct SOA